

217551US

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
YASUTAKA ITO ET AL : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. PCT APPLN :
(Based on PCT/JP01/03759)
FILED: HEREWITH :
FOR: CERAMIC SUBSTRATE FOR
SEMICONDUCTOR
FABRICATING DEVICE

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend the above-identified
application as follows:

IN THE CLAIMS

Please amend Claims 3-6 as follows:

3. (Amended) The ceramic substrate according to claim 1,
wherein the thickness of said ceramic substrate is 25 mm or less.
4. (Amended) The ceramic substrate according to claim 1,
wherein said conductor layer is an electrostatic electrode.
5. (Amended) The ceramic substrate according to claim 1,
wherein said conductor layer is a resistance heating element.

6. (Amended) The ceramic substrate according to claim 1,
wherein said conductor layer is any of a chuck top electrode, a guard electrode and a
ground electrode.

Please add new Claims 7-16 as follows:

7. (New) The ceramic substrate according to claim 2,
wherein the thickness of said ceramic substrate is 25 mm or less.

8. (New) The ceramic substrate according to claim 2,
wherein said conductor layer is an electrostatic electrode.

9. (New) The ceramic substrate according to claim 3,
wherein said conductor layer is an electrostatic electrode.

10. (New) The ceramic substrate according to claim 7,
wherein said conductor layer is an electrostatic electrode.

11. (New) The ceramic substrate according to claim 2,
wherein said conductor layer is a resistance heating element.

12. (New) The ceramic substrate according to claim 3,
wherein said conductor layer is a resistance heating element.

13. (New) The ceramic substrate according to claim 7,
wherein said conductor layer is a resistance heating element.

14. (New) The ceramic substrate according to claim 2,
wherein said conductor layer is any of a chuck top electrode, a guard electrode and a
ground electrode.

15. (New) The ceramic substrate according to claim 3,
wherein said conductor layer is any of a chuck top electrode, a guard electrode and a
ground electrode.

16. (New) The ceramic substrate according to claim 7,
wherein said conductor layer is any of a chuck top electrode, a guard electrode and a
ground electrode.

IN THE ABSTRACT OF THE DISCLOSURE

Please amend the Abstract on page 45 as follows:

ABSTRACT

A ceramic substrate in which even if rapid temperature rising or rapid temperature falling is conducted, no problem of cracking or warp of the ceramic substrate occurs. In a case that the ceramic substrate is a ceramic substrate constituting an electrostatic chuck, local dispersion of chuck power is eliminated, in a case that the ceramic substrate is a ceramic substrate constituting a hot plate, local dispersion of temperature of a wafer treating face is eliminated, and in a case that the ceramic substrate is a ceramic substrate constituting a wafer prober, dispersion of applied voltage of a guard electrode or a ground electrode is eliminated and a stray capacitor or noise can be eliminated. The ceramic substrate is a ceramic substrate provided with a conductor layer on the surface of the ceramic substrate or inside the ceramic substrate, in which the ratio (t_2/t_1) of the average thickness of the conductor layer (t_2) to the average thickness of the ceramic substrate (t_1) is less than 0.1, and a dispersion of the thickness of the conductor layer to the average thickness of the conductor layer is in a range of -70 to +150%.

REMARKS

Favorable consideration of this application, as presently amended, is respectfully requested.

The present preliminary amendment is submitted to place the above-identified application in more proper format under United States practice.

In the preliminary amendment, Claims 3-6 have been amended to no longer recite any improper multiple dependencies. Further, subject matter of the cancelled multiple dependencies is set forth in new dependent Claims 7-16.

The Abstract has also been amended to be in more proper format under United States practice.

The present application is believed to be in condition for a full and thorough examination on the merits. An early and favorable consideration of the present application is hereby respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Gregory J. Maier
Attorney of Record
Registration No. 25,599
Surinder Sachar
Attorney of Record
Registration No. 34,423



22850

(703) 413-3000
Fax No.: (703) 413-2220
GJM/SNS:kst

I:\atty\SNS\217551us-pr.wpd